

Notic of References Cited

Application/Control No.

09/887,199

Applicant(s)/Patent Under
Reexamination
RAAIJMAKERS ET AL.

Examiner

Anh D. Mai

Art Unit

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Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6203613	03-2001	Gates et al.	117/104
	C	US-			
	D	US-			
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	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)			
	U	J.M. Hergenrother et al., 50 nm Vertical Replacement-Gate (VRG) nMOSFETs with ALD HfO2 and Al2O3 Gate Dielectrics. IEDM 2001, pp. 51-54.			
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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